AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

Claims 1-21. (canceled).

22. (original): A group-III nitride semiconductor light-emitting device comprising a single crystal substrate, a boron phosphide (BP)-based buffer layer and a single hetero-junction light-emitting part structure, wherein the single hetero-junction light-emitting part structure containing a $GaN_{1-X}P_X$ ($0<X<1$) lower clad layer lying on the BP-based buffer layer and a $GaN_{1-X}P_X$ light-emitting layer having a conduction type opposite the conduction type of $GaN_{1-X}P_X$ lower clad layer.

23. (original): A group-III nitride semiconductor light-emitting device comprising a single crystal substrate, a boron phosphide (BP)-based buffer layer and a double hetero-junction light-emitting part structure, wherein the double hetero-junction light-emitting part structure containing a $GaN_{1-X}P_X$ ($0<X<1$) lower clad layer, a $Ga_YIn_{1-Y}N$ ($0\leq Y\leq 1$) light-emitting layer and an $Al_ZGa_{1-Z}N$ ($0\leq Z\leq 1$) upper clad layer having a conduction type opposite the conduction type of the lower clad layer.

24. (original): A group-III nitride semiconductor light-emitting device according to claim 1, wherein the lower clad layer has a dislocation density of 1 X 10^5 cm^{-2} to 1 X 10^6 cm^{-2}.

25. (original): A group-III nitride semiconductor light-emitting device according to claim 1, wherein the lattice mismatch between the lower clad layer and the light-emitting layer is 0.3% at most.

26. (original): A group-III nitride semiconductor light-emitting device according to claim 1, wherein the light-emitting layer has a dislocation density of 2 X 10^5 cm^{-2} to 1 X 10^6 cm^{-2}.

27. (original): A group-III nitride semiconductor light-emitting device according to claim 1, wherein the buffer layer has the lattice constant of the original crystal of the material on the buffer layer surface opposite the junction interface with the substrate and the thickness of 5 nm to 50 nm.